

ABSTRACT OF THE DISCLOSURE

A solid-state imaging device includes unit cells, arranged in a matrix of rows and columns, each having a photodiode for photoelectrically converting incident light to store signal charges, a readout transistor Td for reading out the signal charges and amplifying transistor Tb for amplifying signals readout at a detection node, a plurality of vertical shift registers for generating signal charge readout pulses ESi, DRi, ROi and a voltage switching circuit for setting a voltage VDR of the readout pulse DRi for dynamic range control lower than voltages of both a readout pulse ESi for an electronic shutter and a usual readout pulse ROi. The solid-state imaging device provides excellent images without clipping from a small signal region to large signal region.